



P-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} -60V
- I_{D25}



Typical Performance Characteristics

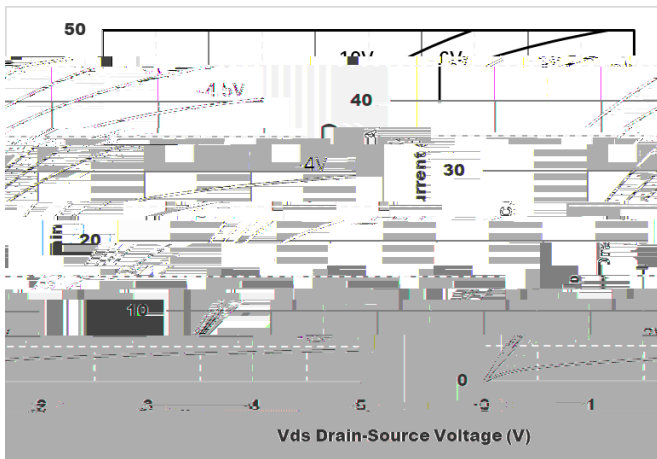


Figure1. Output Characteristics

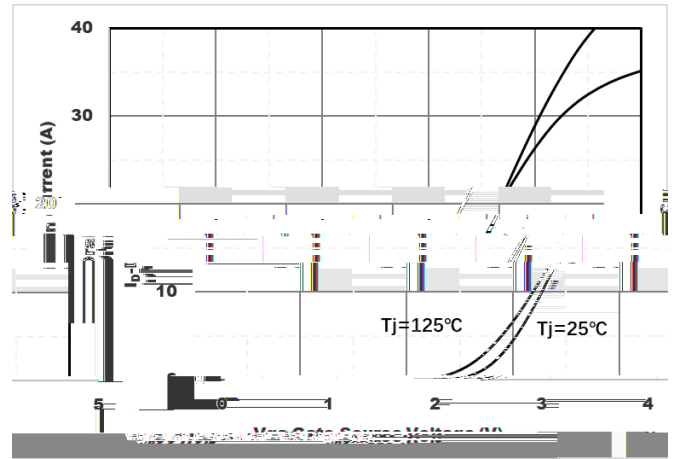


Figure2. Transfer Characteristics

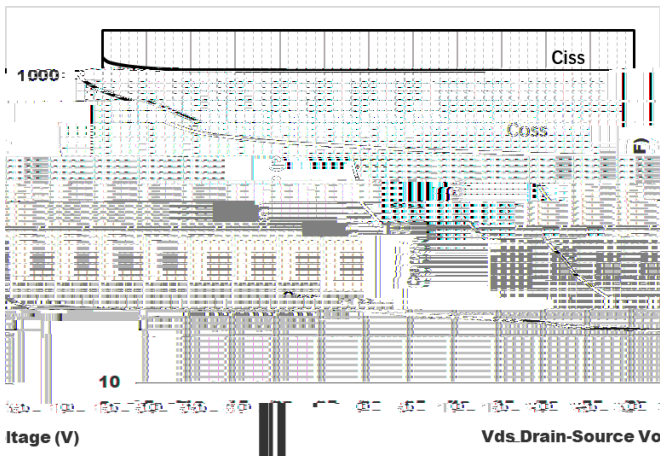


Figure3. Capacitance Characteristics

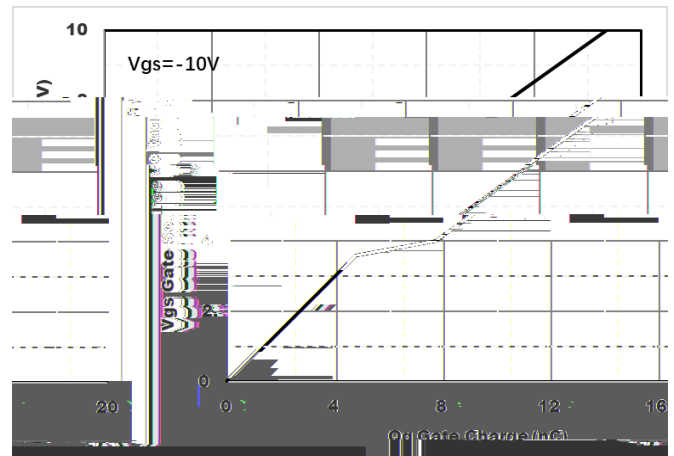


Figure4. Gate Charge

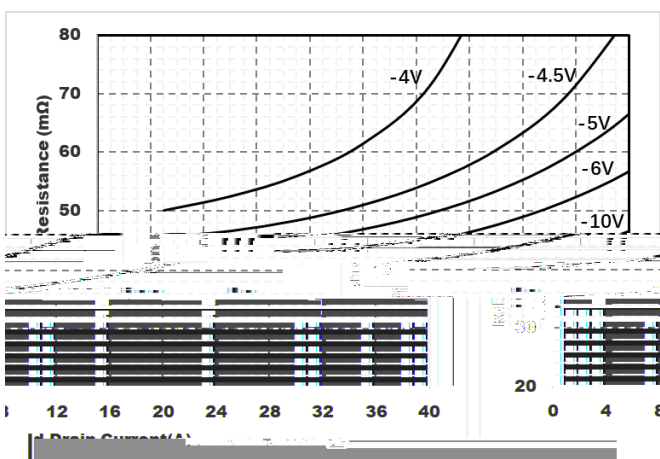


Figure5. : On-Resistance vs. Drain Current

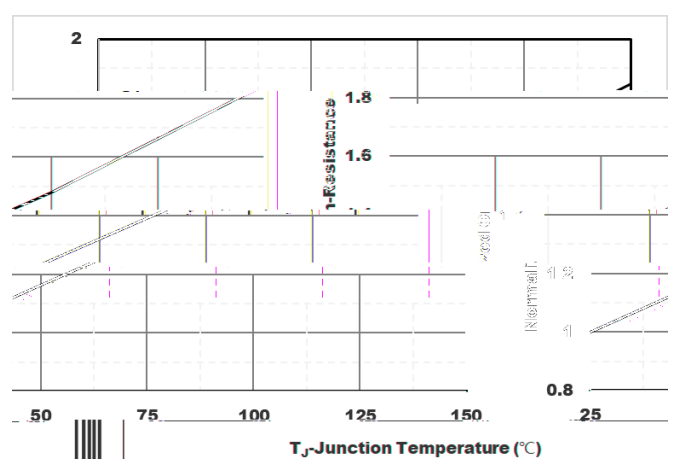


Figure6. Normalized On-Resistance



Figure7. Normalized Gate Threshold Voltage

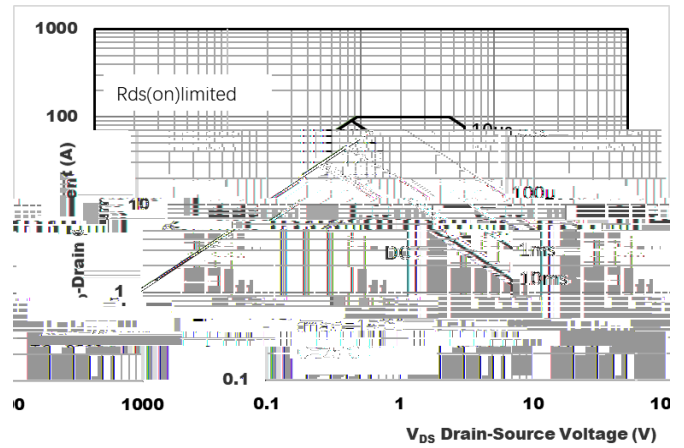


Figure8.Safe Operation Area

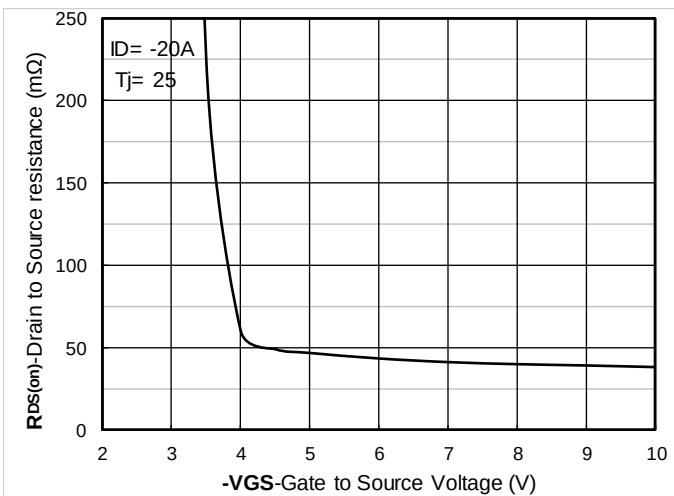


Figure 9. On-Resistance vs Gate to Source Voltage

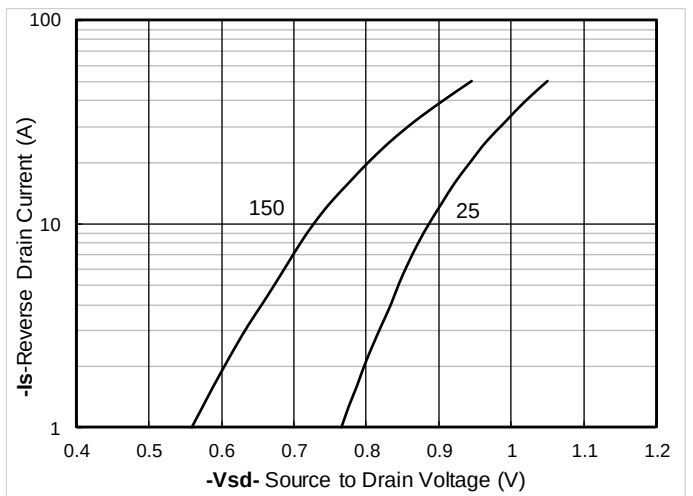


Figure 10. Forward characteristics of reverse diode

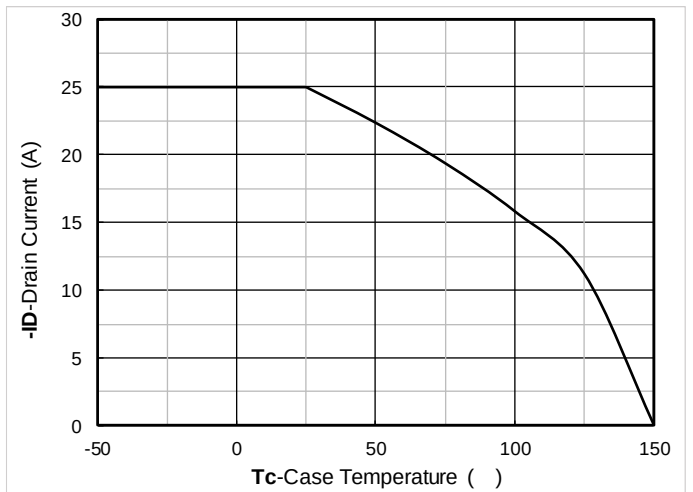


Figure 11. Normalized breakdown voltage

Figure 12. Current dissipation

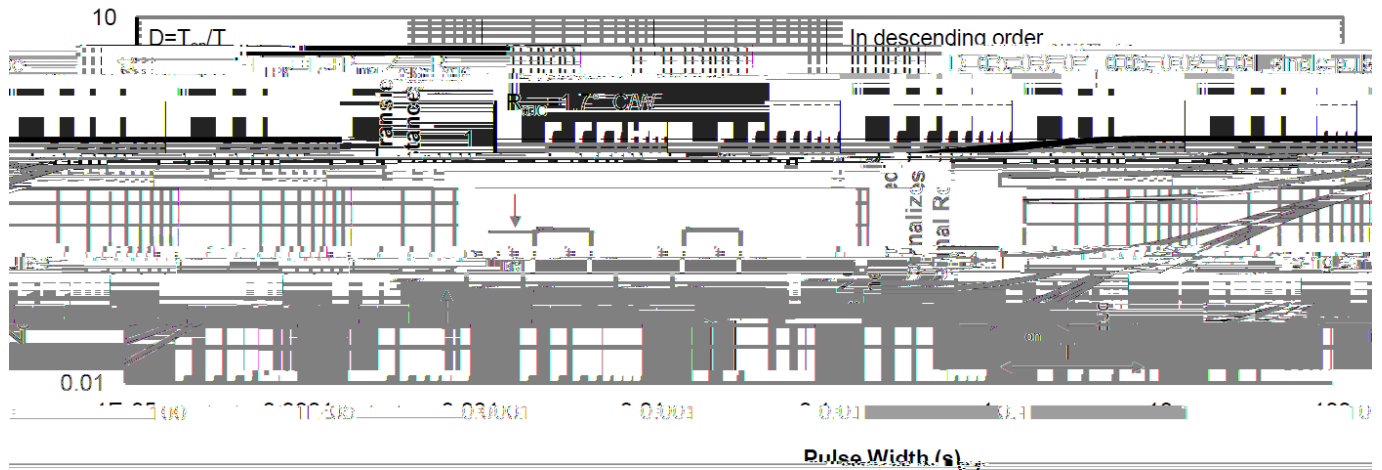
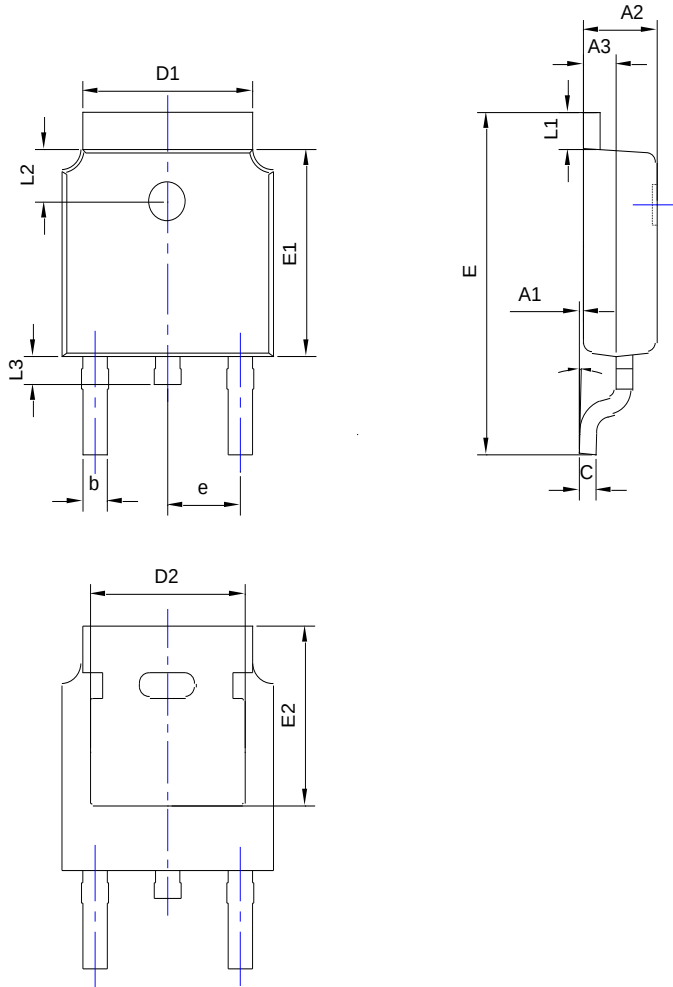


Figure13.Normalized Maximum Transient thermal impedance



YJD25GP06A

TO-252-B Package information



SYMBOL	DIMENSIONS				
	INCHES				
	MIN.	NOM.			
A1	0.000				
A2	0.087	0.091			
A3	0.035	0.039			
b	0.026	0.030			
c	0.018	0.020			
D	0.256	0.260			
D1					
D2	0.181	0.189			
E	0.390	0.398			
E1	0.236	0.240			

NOTE:

- 1.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2.TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3.THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

